consisting of Au, Pt, Fe and Al.

11. (Amended) The method of fabricating a thin film transistor according to claim 9, wherein at least a first electrode and a second electrode are formed prior to the crystallizing step [the electrodes includes first and second electrodes], and crystallization of the amorphous silicon layer occurs faster at the first electrode than at the second electrode.

12. (Amended) The method of fabricating a thin film transistor according to claim 9, wherein at least [the electrodes includes] a negative electrode and a positive electrode are formed prior to the crystallizing step, and crystallization of the amorphous silicon layer occurs faster at the negative electrode than at the positive electrode.

Claim 21, line 3, please delete "is".

23. (Amended) The method of fabricating a thin film transistor according to claim 21, wherein at least a first electrode and a second electrode are formed [the electrodes includes first and second electrodes], and crystallization of the amorphous silicon layer occurs faster at the first electrode than at the second electrode.

Please add the following new Claims 25-36.

--25. A method of fabricating a thin film transistor comprising the steps of:

forming an amorphous silicon layer as an active layer on a substrate;

forming a gate insulating layer and a gate electrode on the amorphous silicon layer;

forming a metal layer on exposed portions of the amorphous silicon layer;

doping impurities of a first conductive type in the amorphous silicon layer after the metal layer is formed; and

crystallizing the amorphous silicon layer by applying thermal treatment and an electric field to the resultant substrate.

~~26. The method of fabricating a thin film transistor according to claim 25, wherein the~~

substrate includes one of a glass and an oxide layer on a glass.

27. The method of fabricating a thin film transistor according to claim 25, wherein the substrate is prepared by depositing a silicon wafer or an oxide layer on a silicon wafer.

28. The method of fabricating a thin film transistor according to claim 25, wherein the gate electrode is formed by at least one transition metal selected from the group consisting of Mo, Cr and Co.

29. The method of fabricating a thin film transistor according to claim 25, wherein the impurities include PH_3.

30. The method of fabricating a thin film transistor according to claim 25, wherein the metal layer has a thickness of no more than 30Å.

31. The method of fabricating a thin film transistor according to claim 30, wherein the metal layer is formed by at least one transition metal selected from the group consisting of Cu, Ni, Fe, Co, Ru, Rh, Pd, Os, Ir, Pt, Se, Ti, V, Cr, Mn, Zn, Au and Ag.

32. The method of fabricating a thin film transistor according to claim 25, wherein the heat treatment is performed at about 500°C.

33. The method of fabricating a thin film transistor according to claim 25, further comprising a step of forming electrodes for applying a voltage to form the electric field on the resultant substrate.

34. The method of fabricating a thin film transistor according to claim 33, wherein the electrodes are formed by a metal selected from the group consisting of Au, Pt, Fe and Al.

35. The method of fabricating a thin film transistor according to claim 33, wherein at least a first electrode and a second electrode are formed prior to the crystallizing step, and crystallization of the amorphous silicon layer occurs faster at the first electrode than at the second electrode.